

# N-channel 25 V 6.5 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 31 October 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

#### 1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	25	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	64	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	48	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
03011	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	7.3	8.5	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 20 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 12	-	5.5	6.5	mΩ
Dynamic o	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 12 \text{ V};$	-	2.8	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15	-	8.4	-	nC



### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb (	D
3	S	source		。( <mark>巨大</mark> )
4	G	gate	[q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R5-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	25	V
$V_{DGR}$	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 k $\Omega$	-	25	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \frac{\text{Figure 1}}{\text{Model}}$	-	64	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	45	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4	-	256	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	48	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
$V_{ESD}$	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	240	-	V
Source-dra	ain diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	44	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	256	Α
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 64 A; $V_{sup} \le$ 25 V; unclamped; $R_{GS}$ = 50 Ω; see Figure 3	-	18	mJ

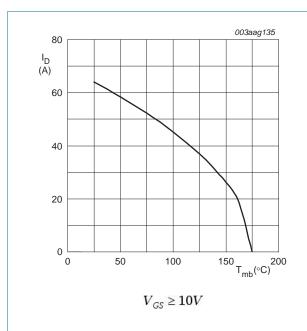


Fig 1. Continuous drain current as a function of mounting base temperature

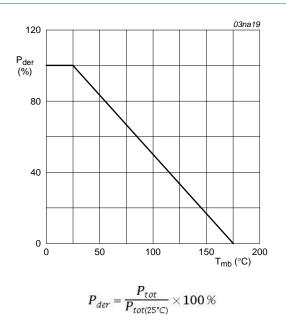


Fig 2. Normalized total power dissipation as a function of mounting base temperature

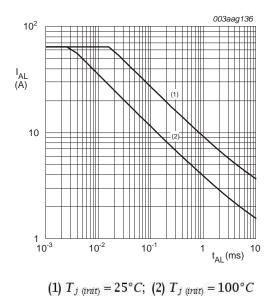


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

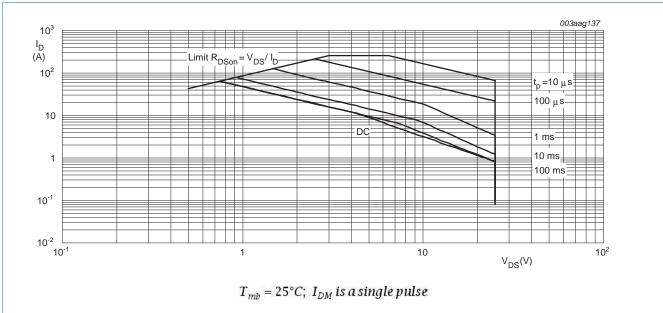
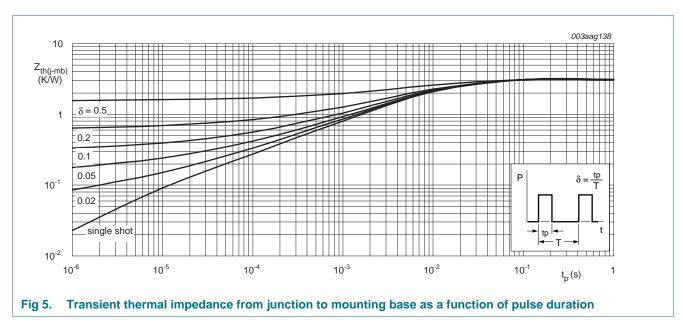


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.9	3.13	K/W



### 6. Characteristics

Table 6. Characteristics

	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10; see Figure 11	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	7.3	8.5	mΩ	
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 13; see Figure 12	-	-	13.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	5.5	6.5	mΩ
	$V_{GS}$ = 10 V; $I_D$ = 20 A; $T_j$ = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	10.3	mΩ	
$R_G$	internal gate resistance (AC)	f = 1 MHz	-	2.2	4.4	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	total gate charge	$I_D = 20 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	17.5	-	nC
		$I_D = 20 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8.4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	16	-	nC
$Q_{GS}$	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	0.9	-	nC
$Q_{GD}$	gate-drain charge		-	2.8	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 20 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; see Figure 14; see Figure 15	-	2.71	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1093	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	282	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	106	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 12 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	8.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	5.7	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz}$	-	5.7	-	nC
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.86	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	24	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	15	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$	-	14	-	ns
t <sub>b</sub>	reverse recovery fall time	$dI_S/dt = -100 A/\mu s; V_{DS} = 12 V;$ see Figure 18	-	10	-	ns

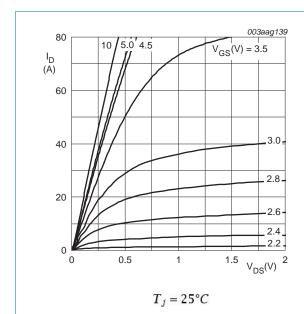
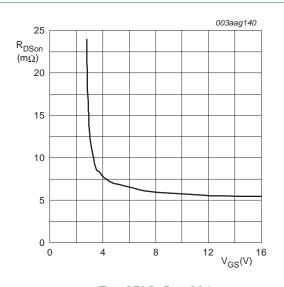


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

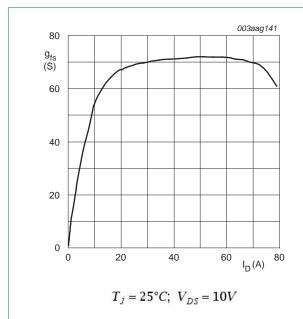


Fig 8. Forward transconductance as a function of drain current; typical values

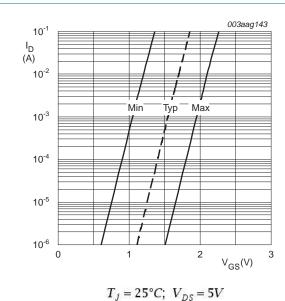


Fig 10. Sub-threshold drain current as a function of gate-source voltage

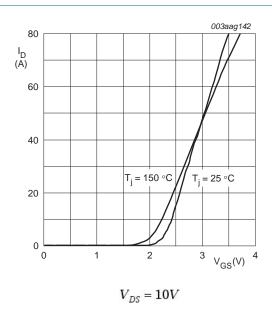


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

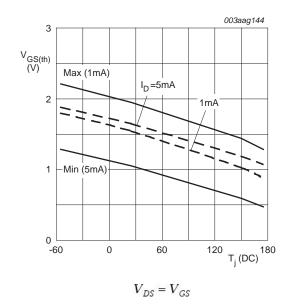


Fig 11. Gate-source threshold voltage as a function of junction temperature

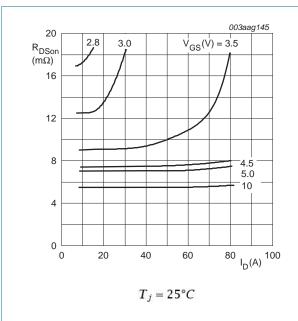


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

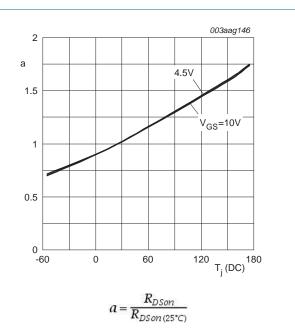


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

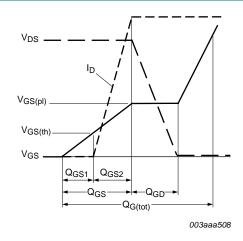
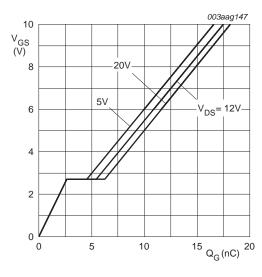


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

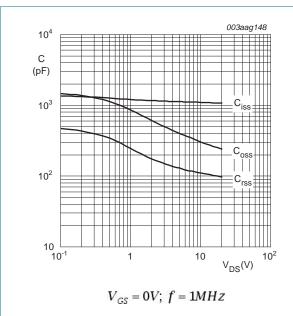


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

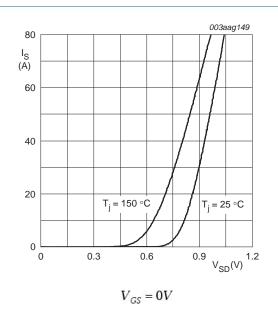


Fig 17. Source current as a function of source-drain voltage; typical values

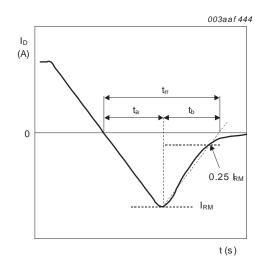
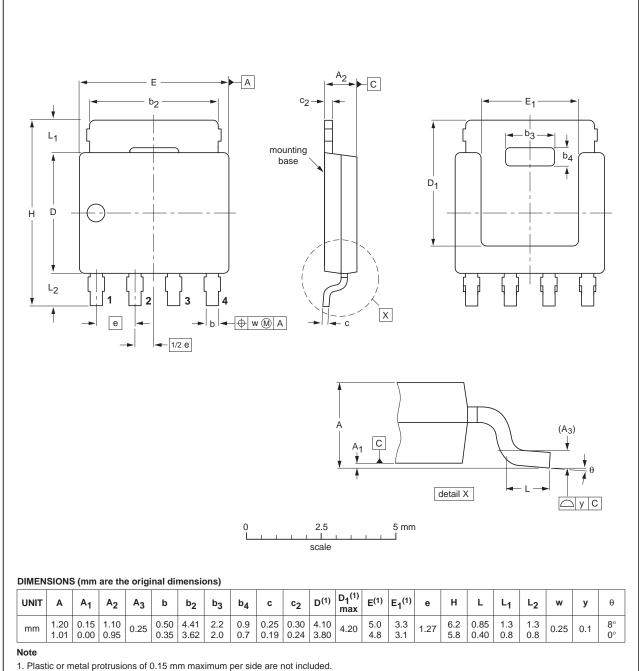


Fig 18. Reverse recovery timing definition

### Package outline

### Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

**SOT669** 



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT669		MO-235			<del>06-03-16</del> 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN6R5-25YLC

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N-channel 25 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R5-25YLC v.2	20111031	Product data sheet	-	PSMN6R5-25YLC v.1
Modifications:	<ul> <li>Status changed from</li> </ul>	om objective to product.		
	<ul> <li>Various changes to</li> </ul>	o content.		
PSMN6R5-25YLC v.1	20110712	Objective data sheet	-	-

#### N-channel 25 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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### **Nexperia**

# PSMN6R5-25YLC

N-channel 25 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

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